DG2034E

Vishay Siliconix



Power Down Fault Protected, 1.8 V to 5.5 V, 2.5 Ω , 4-Channel (4:1) Multiplexer

DESCRIPTION

The DG2034E is a four-channel multiplexer that operates with a single 1.8 V to 5.5 V power supply. It features power down fault protection that prevents excessive current flow when V+ is to ground.

The device's low power dissipation and wide voltage range make it ideal for use in battery powered products. The ultra low capacitance and charge injection of the switch make it an ideal solution for data acquisition and sample and hold applications, where low glitch and fast settling are required. Low switch resistance and fast switching speeds, together with high signal bandwidth, make the DG2034E suitable for video signal switching.

The DG2034E switches one of four inputs to a common output as determined by the 3-bit binary address lines: A0, A1, and EN. Each switch conducts equally well in both directions when on, blocks input voltages up to the supply level when off, and exhibits break before make switching action.

The device's high ESD and latch-up current capability make it more reliable in designs where the part sits close to the interface.

The DG2034E is available in MSOP10 and QFN12 3 mm x 3 mm packages.

FEATURES

- 2.5 Ω switch on-resistance
- 7 pF source-off capacitance
- 27 pF comm-off capacitance
- 33 pF comm-on capacitance
- 13 ns turn-on time
- -2 pC charge injection
- -67 dB off-isolation at 1 MHz
- -71 dB crosstalk at 1 MHz
- 166 MHz bandwidth
- 8 kV ESD / HBM
- 400 mA latch-up current

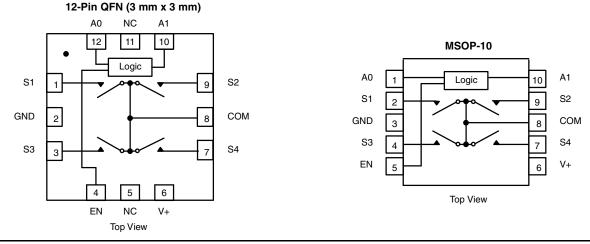
BENEFITS

- Power down fault protection
- Low parasitic and charge injection
- Wide operation voltage range
- High ESD tolerance

APPLICATIONS

- Automatic test equipment
- Process control and automation
- Data acquisition systems
- Meters and instruments
- · Medical and healthcare systems
- · Communication systems
- · Audio and video switching
- · Relay replacements

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



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TRUTH TABLE							
A1	A0	EN	ON SWITCH				
Х	Х	0	None				
0	0	1	S1				
0	1	1	S2				
1	0	1	S3				
1	1	1	S4				

ORDERING INFORMATION					
TEMP. RANGE	PACKAGE	PART NUMBER			
-40 °C to +85 °C	MSOP-10	DG2034EDQ-T1-GE3			
	12-pin QFN (3 mm x 3 mm)	DG2034EDN-T1-GE4			

PARAMETER		LIMIT	UNIT	
Referenced V+ to GND		-0.3 to +6	v	
A _X , EN, S _X , COM ^a		-0.3 to (V+ + 0.3)	v	
Continuous current (any terminal)		± 50		
Peak current (pulsed at 1 ms, 10 % duty cy	± 100	— mA		
Power dissipation (package) ^b	QFN-12 (3 mm x 3 mm) ^c	1295		
	MSOP-10 d	320	mW	
Storage temperature (D suffix)		-65 to +150	°C	
ESD / HBM	EIA / JESD22-A114-A	8k	V	
ESD / CDM	EIA / JESD22-C101-A	2k	V	
Latch up	JESD78	400	mA	

Notes

a. Signals on S_X, COM, EN or A_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings

b. All leads welded or soldered to PC board

c. Derate 16.2 mV/°C above 70 °C

d. Derate 4 mV/°C above 70 °C



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SPECIFICATIONS (V+ =	3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPEC	TEMP. ^a	LIMITS -40 to +85 °C			UNIT	
		V+ = 3 V, \pm 10 %, V _{AL} = 0.5 V, V _{AH}	_H = 1.5 V ^e		MIN. ^c	TYP. ^b	MAX. °	
Analog Switch								
Analog signal range ^d	V _{ANALOG}				0	-	V+	V
Drain-source On-resistance		$V_{+} = 1.8 V, V_{S} = 0.4 V / V_{+}, I_{S} = 8 mA$			-	7	10	
	R _{DS(on)}		Full	-	-	11		
	US(on)	V+ = 2.7 V, V_{COM} = 0.8 V / 1.8 V I _{COM} = 10 mA		Room	-	4.6		5.3
				Full	-	-	5.9	Ω
On-resistance matching	$\Delta R_{DS(on)}$		Room	-	0.02	0.27		
	DO(01)	$V_{+} = 2.7 V, V_{COM} = 0.8 V / 1.4 V$	/ / 1.8 V	Full	-	-	0.41	
On-resistance flatness ^{d, f}	R _{flat(on)}	I _{COM} = 10 mA		Room	-	0.62	1	
	nation			Full	-	-	1.3	
Off leakage current ^g	I _{S(off)}			Room	-2	0.01	2	
5	0(01)	$V_{+} = 3.3 V, V_{S} = 1 V / 3 V$		Full	-5	-	5	
COM off leakage current ^g	I _{COM(off)}	V _{COM} = 3 V / 1 V, V _{EN} = 0	V	Room	-2	0.01	2	nA
				Full	-5	-	5	
Channel-on leakage current ^g	I _{COM(on)}	$V_{+} = 3.3 V$		Room	-2	0.01	2	
	e e ini(eii)	$V_{COM} = V_S = 1 V / 3 V$	Full	-5	-	5		
Digital Control							I .	· ·
Input current d	I _A or I _{EN}	$V_{A/EN} = 0 V \text{ or } V+$, see truth table		Full	-1	0.05	1	μA
Input high voltage d	V _{AH} or V _{ENH}			Full	1.5	1.25	-	V
Input low voltage d	V _{AL} or V _{ENL}			Full	-	1	0.5	-
Digital input capacitance d	C _{IN}			Room	-	3	-	pF
Dynamic Characteristics		Г		Deere		10	00	-
Turn-on time	t _{ON}			Room	-	19	29	-
	-			Full	-	-	39	
Turn-off time	t _{OFF}	$V_{S} = 1.5 V, C_{L} = 35 pF, R_{L} = 35$	300 Ω	Room	-	16	26	
				Full	-	- 10	36	ns
Break-before-make time ^d	t _{BBM}			Room Full	7 5	12	-	
				-	- -	- 26		
Transition time	t _{trans}	$V_{S} = 1.5 \text{ V} / 0 \text{ V}, V_{S} = 0 \text{ V} / 1.5 \text{ V}, \text{ F}$	$R_L = 300 \ \Omega$	Room Full	-	- 20	41 51	
Charge injection d	0	C _L = 1 nF, V _{gen} = 1.5 V, R _{gen} =	-00	Room	-	-2	-	рС
Bandwidth ^d	Q _{INJ} BW	$C_L = 5 \text{ pF}$ (set up capacitar		Room	-	166	-	MHz
Bandwidth	BW	CL = 5 pr (set up capacital	f = 1 MHz	Room	-	-67	-	IVITIZ
Off-isolation ^d	OIRR	$R_L = 50 \Omega, C_L = 5 pF$	f = 10 MHz	Room	-	-52	-	
	X _{TALK}	$R_{L} = 50 \Omega, C_{L} = 5 pF \qquad \frac{f = 1 MHz}{f = 10 MHz}$		Room	-	-71	_	dB
Channel-to-channel crosstalk ^d			Room	_	-55	_	-	
Off capacitance d	C _{S(off)}	V+ = 2.7 V, f = 1 MHz		Room	_	7	-	pF
COM off capacitance d	C _{COM(off)}			Room	-	27	-	
COM on capacitance ^d	C _{COM(off)}			Room	-	33	-	
Power Supply				Hoom	I		I	L
Power supply range	V+			Full	2.7	-	3.3	V
Power supply current d	V+ +	V+ = 2.7 V, V _{A/EN} = 0 V or 2.7 V, see	Full	-	-	1	μA	
Notes					I	1	l '	۳' ۱

Notes

a. Room = 25 °C, Full = as determined by the operating suffix

b. Typical values are for design aid only, not guaranteed nor subject to production testing

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

d. Guarantee by design, not subjected to production test

e. V_A, EN = input voltage to perform proper function

f. Difference of min. and max. values

g. Guaranteed by 5 V testing

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SPECIFICATIONS (V+ =	5 V)							
		TEST CONDITIONS			LIMITS -40 to +85 °C			
PARAMETER	SYMBOL	OTHERWISE UNLESS SPE V+ = 5 V, ± 10 %, V _{AL} = 0.5 V, V		TEMP. ^a	-4 MIN. °	TYP. b	MAX. °	UNIT
Analog Switch	<u> </u>				1	1		
Analog signal range d	V _{ANALOG}			Full	0	-	V+	V
Drain-source	_	$V_{+} = 4.5 V. V_{COM} = 0.8 V / 3.5 V$			-	2.5	3.1	<u> </u>
On-resistance	R _{DS(on)}	V+ = 4.5 V, V _{COM} = 0.8 V / I_{COM} = 10 mA	Full	-	-	4		
On-resistance matching	$\Delta R_{DS(on)}$				-	0.02	0.29	Ω
On-resistance matching	ZI (DS(on)	V + = 4.5 V, V_{COM} = 0.8 V / 2.5	V / 3.5 V	Full	-	-	0.42	52
On-resistance flatness ^{d, f}	R _{flat(on)}	$I_{COM} = 10 \text{ mA}$		Room	-	0.6	0.9	
	flat(on)			Full	-	-	1.2	
Off leakage current ^g	I _{S(off)}			Room	-2	0.17	2	
	15(011)	$V + = 5.5 V, V_S = 1 V / 4.5$	5 V	Full	-8	-	8	
COM off leakage current ^g	I _{COM(off)}	V _{COM} = 4.5 V / 1 V, V _{EN} =	0 V	Room	-5	0.77	5	nA
Com on loanage carrent	-COM(OII)			Full	-15	-	15	1.2 (
Channel-on leakage current ^g	I _{COM(on)}	V+ = 5.5 V, V _{COM} = V _S = 1 V	/ 4.5 V	Room	-5	0.61	5	
	COM(on)			Full	-15	-	15	
Power down leakage ^d	I _{PD}	$V+ = 0 V, V_D = 5.5 V, S_X c$	pen	Full	-	0.01	5	μA
i ower down leakage	PD	V + = 0 V, V_S = 5.5 V, COM, open		Full	-	0.01	5	μ/ (
Digital Control						-		
Input current ^d	I_A or I_{EN}	$V_{A/EN} = 0$ V or V+, see truth	Full	-	0.01	1	μA	
Input high voltage ^d	$V_{\text{AH}} \text{ or } V_{\text{ENH}}$			Full	2	1.76	-	v
Input low voltage ^d	V_{AL} or V_{ENL}		Full	-	1.3	0.5] ^v	
Digital input capacitance ^d	C _{IN}			Room	-	3	-	pF
Dynamic Characteristics								
Turn-on time	+			Room	-	13	25	
rum-on time	t _{ON}			Full	-	-	35	
Turn-off time	t	V _S = 3 V, C _L = 35 pF, R _L = 3	200 0	Room	-	12	20	
rum-on time	t _{OFF}	$v_{\rm S} = 3 v, O_{\rm L} = 33 pr, H_{\rm L} = 3$	300 12	Full	-	-	30	-
Break-before-make time ^d	+			Room	4	10	-	ns
Break-belore-make time a	t _{BBM}			Full	3	-	-	
Turne siting time a			000 0	Room	-	17	32	
Transition time	t _{trans}	$V_{S} = 3 V / 0 V, V_{S} = 0 V / 3 V, R$	$L = 300 \Omega$	Full	-	-	42	
Propagation delay ^d	t _{PD}	$V + = 5 V$, no R_{LOAD}		Room	-	537	-	ps
Charge injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{gen} = 2.5 \text{ V}, R_{ger}$	$n = 0 \Omega$	Room	-	-2.6	-	рС
Bandwidth ^d	BW	C _L = 5 pF (set up capacita	ance)	Room	-	166	-	MH
Off is a lation d			f = 1 MHz	Room	-	-67	-	1
Off-isolation ^d	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$	f = 10 MHz	Room	-	-52	-	
Ohan and the alternation of all d	X		f = 1 MHz	Room	-	-71	-	dB
Channel-to-channel crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$	f = 10 MHz	Room	-	-55	-	
Off capacitance d	C _{S(off)}	V+ = 5 V, f = 1 MHz		Room	-	7	-	
COM off capacitance d	C _{COM(off)}			Room	-	27	-	pF
COM on capacitance d	C _{COM(on)}			Room	-	36	-	
Power Supply								
Power supply range	V+			Full	4.5	-	5.5	V
Power supply current ^d	l+	$V_{+} = 5.5 V, V_{A/EN} = 0 V \text{ or } 5.5 V, set{tabular}$	e truth table	Full	-	-	1	μA

Notes

a. Room = 25 °C, Full = as determined by the operating suffix

b. Typical values are for design aid only, not guaranteed nor subject to production testing

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

d. Guarantee by design, not subjected to production test

e. V_A , EN = input voltage to perform proper function

f. Difference of min. and max. values

g. Guaranteed by 5 V testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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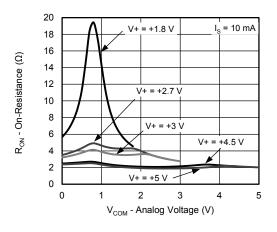
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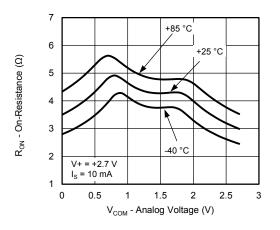


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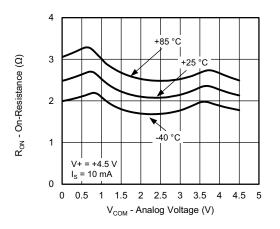
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



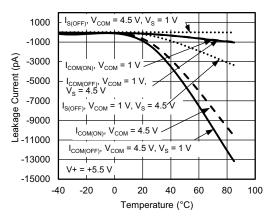
On-Resistance vs. Analog Voltage



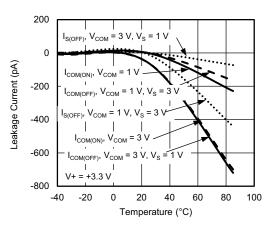
On-Resistance vs. Analog Voltage



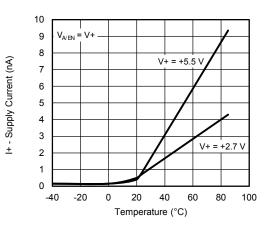
On-Resistance vs. Analog Voltage



Leakage Current vs. Temperature



Leakage Current vs. Temperature



Supply Current vs. Temperature

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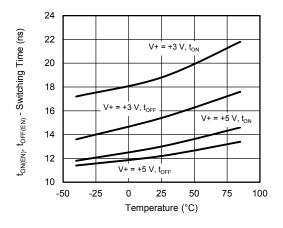
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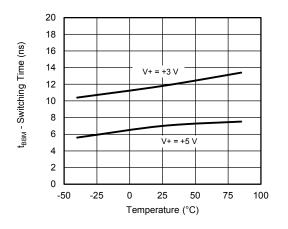


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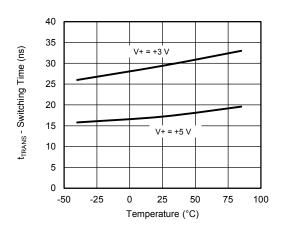
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



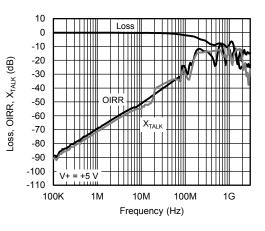
Switching Time vs. Temperature



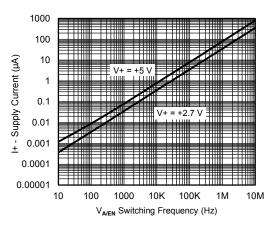
Switching Time vs. Temperature



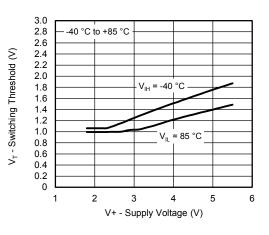
Switching Time vs. Temperature



Loss, OIRR, X_{TALK} vs. Frequency



Positive Supply Current vs. Switching Frequency



Switching Threshold vs. Supply Voltage

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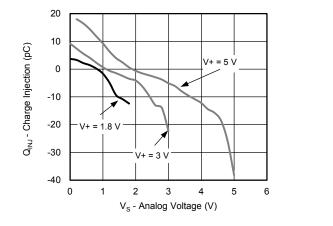
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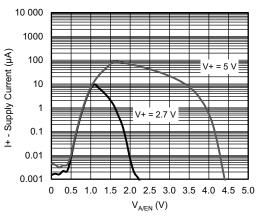


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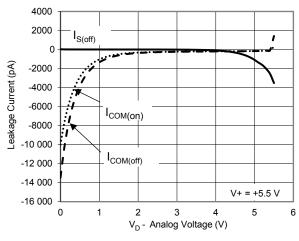
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Charge Injection vs. Source Voltage



Positive Supply Current vs. Logic Voltage

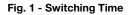


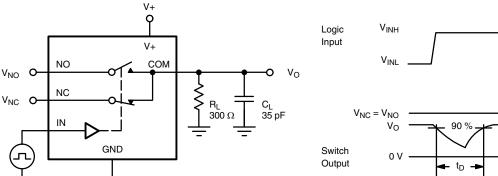
Leakage Current vs. Analog Voltage

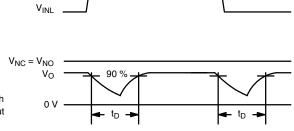
q Switch V+

V_{INL} O VOUT VOUT 0 V Switch Output ton

> Logic input waveform is inverted for switches that Note: have the opposite logic sense control

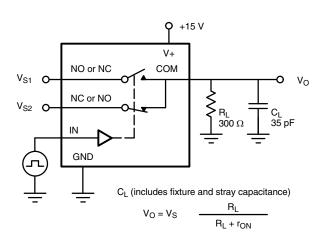


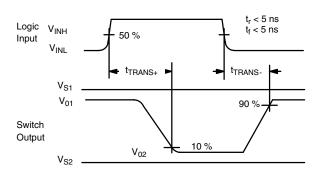




CL (includes fixture and stray capacitance)





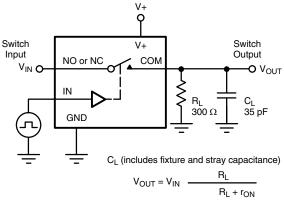




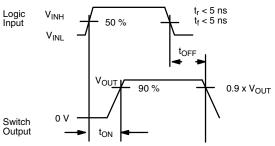
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TEST CIRCUITS

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t_r < 5 ns

t_f < 5 ns

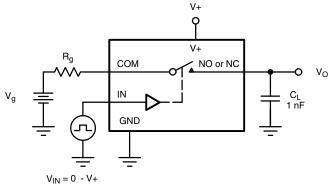
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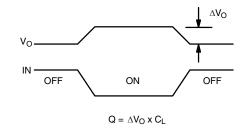


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TEST CIRCUITS





IN dependent on switch configuration Input polarity determined by sense of switch.

Fig. 4 - Charge Injection

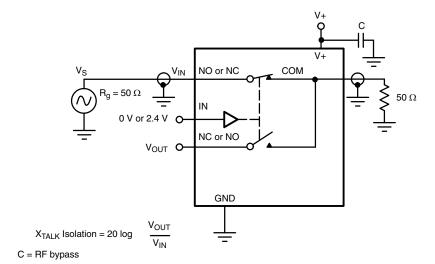
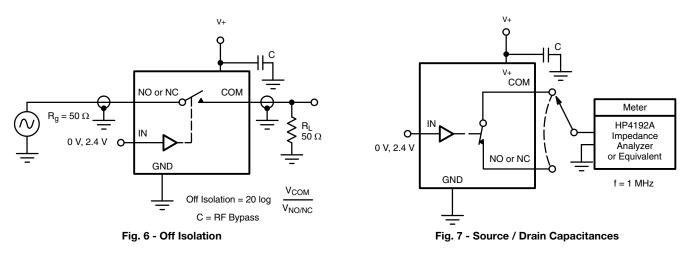


Fig. 5 - Crosstalk





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TEST CIRCUITS

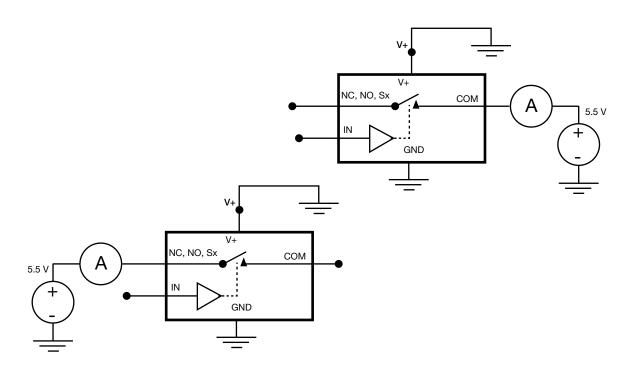


Fig. 8 - Source / Drain Power Down Leakage

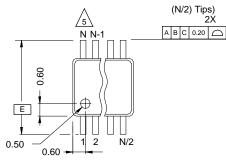
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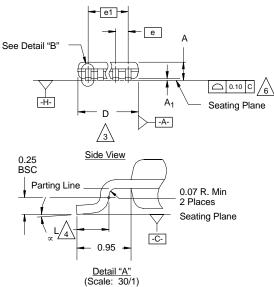
Package Information Vishay Siliconix

MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)







NOTES:

/4.\

/5.\

1. Die thickness allowable is 0.203 ± 0.0127 .

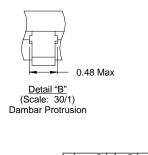
2. Dimensioning and tolerances per ANSI.Y14.5M-1994.

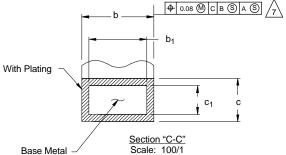
- /3. Dimensions "D" and "E₁" do not include mold flash or protrusions, and are measured at Datum plane _-H- , mold flash or protrusions shall not exceed 0.15 mm per side.
 - Dimension is the length of terminal for soldering to a substrate.

Terminal positions are shown for reference only.

- 6. Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.
- The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".
- /8. Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.
- 9. Controlling dimension: millimeters.
- 10. This part is compliant with JEDEC registration MO-187, variation AA and BA.
- 11. Datums -A- and -B- to be determined Datum plane -H-.

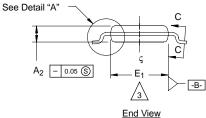
 $\cancel{12}$ Exposed pad area in bottom side is the same as teh leadframe pad size.





(See Note 8)





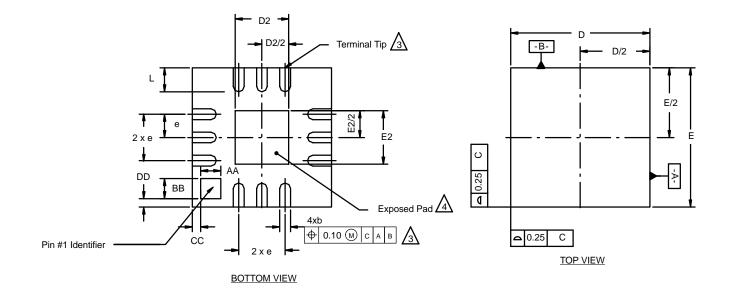
N = 10L

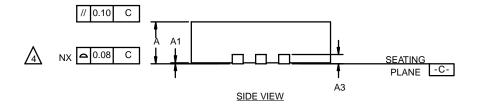
	M	MILLIMETERS				
Dim	Min	Nom	Max	Note		
Α	-	-	1.10			
A ₁	0.05	0.10	0.15			
A ₂	0.75	0.85	0.95			
b	0.17	-	0.27	8		
b ₁	0.17	0.20	0.23	8		
С	0.13	-	0.23			
c ₁	0.13	0.15	0.18			
D		3				
Е		4.90 BSC				
E ₁	2.90	3.00	3.10	3		
е		0.50 BSC				
е ₁		2.00 BSC				
L	0.40	0.55	0.70	4		
Ν		5				
x	0°	4°	6°			
ECN: T-02 DWG: 58	2080—Rev. (67	C, 15-Jul-02				



Package Information Vishay Siliconix

QFN-12 LEAD (3 X 3)





		MILLIMETERS			INCHES			
	Dim	Min	Nom	Max	Min	Nom	Max	
	Α	0.80	0.90	1.00	0.032	0.035	0.039	
e in millimeters.	b	0.18	0.23	0.30	0.007	0.009	0.012	
ber of terminals.	D	3.00 BSC			0.118 BSC			
lies to metallized terminal and is measured	D2	1.00	1.15	1.25	0.039	0.045	0.049	
d 0.30 mm from terminal tip.	E	3.00 BSC			0.118 BSC			
es to the exposed heat sink slug as well as the	E2	1.00	1.15	1.25	0.039	0.045	0.049	
	е		0.50 BSC			0.02 BSC		
fier may be either a mold or marked feature, it within the zone iindicated.	L	0.45	0.55	0.65	0.018	0.022	0.026	
within the zone indicated.	AA	0.435			0.017			
	BB	0.435			0.017			
	CC	0.18			0.007			
	DD		0.18			0.007		
	ECN: C-03092—Rev. A, 14-Apr-03 DWG: 5898							

NOTES:

- 1. All dimensions are
- 2. N is the total numb



Dimension b applie between 0.25 and

- <u>/4</u>. Coplanarity applies terminal.
- 5. The pin #1 identifie must be located w



Vishay

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